

**Amendments to the Specification:**

Please replace the paragraph at page 11, lines 15-24, with the following amended paragraph:

Embodiments of methods of forming the dielectric layer 16 by the atomic layer deposition method at a temperature condition of about 600°C or less will now be further described. First, the temperature of the inner portion of the processing chamber is set to about 600°C ~~or less~~ and, in some embodiments, to about 450°C. Then, a third reacting material is introduced into the processing chamber. The third reacting material is selected based on the kind of the thin film to be formed. When forming a metal oxide layer, the third reacting material may include a metal precursor. A portion of the introduced third material is chemically absorbed on the reaction-inhibiting protection layer 14.